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It is further certified that the student has fulfilled all the requirements of comprehensive examination, candidacy and SOTA for the award of Ph.D. Degree.

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## DECLARATION BY THE CANDIDATE

I, "**Debarati Pal**", certify that the work embodied in this thesis is my own bonafide work and carried out by me under the supervision of "**Dr. Swapnil Patil**" from "**July 2017**" to "**July 2022**", at the "**Department of Physics**", Indian Institute of Technology (BHU), Varanasi. The matter embodied in this thesis has not been submitted for the award of any other degree/diploma. I declare that I have faithfully acknowledged and given credits to the research workers wherever their works have been cited in my work in this thesis. I further declare that I have not willfully copied any other's work, paragraphs, text, data, results, *etc.*, reported in journals, books, magazines, reports dissertations, theses, *etc.*, or available at websites and have not included them in this thesis and have not cited as my own work.

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It is certified that the above statement made by the student is correct to the best of my/our knowledge.

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(Debarati Pal)



*I dedicate this thesis to my beloved parents*

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# Contents

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<b>Certificate</b>	<b>iii</b>
<b>Declaration by the Candidate</b>	<b>v</b>
<b>Copyright Transfer Certificate</b>	<b>vii</b>
<b>Acknowledgements</b>	<b>ix</b>
<b>Contents</b>	<b>xv</b>
<b>List of Figures</b>	<b>xviii</b>
<b>List of Tables</b>	<b>xxv</b>
<b>Preface</b>	<b>xxvii</b>
<b>Chapter 1: Introduction: A bibliographic review</b>	<b>33-56</b>
1.1 Introduction	35
1.2 Topology in geometry	38
1.3 The concept of Topology in integer quantum Hall effect	39
1.4 The tour from quantum hall to quantum spin hall effect	40
1.5 Topological Insulator to Topological Semimetals	43
1.4.1 Weyl Semimetals	46
1.6 Magnetic Topological materials	49
1.6.1 Quantum oscillation	53
1.7 Topological Insulator under Pressure	54
1.7.1 Crystal structure and Symmetry Properties under pressure	56
<b>Chapter 2: Methodology and Characterization tools</b>	<b>57-76</b>
2.1 Introduction	59
2.1.1 Modified Bridgeman technique	59
2.1.2 Chemical vapour transport technique	60
2.2 Experimental characterization tools	61
2.2.1 X-Ray diffraction (XRD)	61
2.3 Transport property measurements	63
2.3.3.1 Electric resistivity ( $\rho_{xx}$ )	63
2.4 Magnetic property measurement System (MPMS)	67
2.4.1 DC magnetization and AC susceptibility	67
2.5 Raman Spectroscopy	69
2.6 High Pressure Techniques	71
2.7 Fundamentals of ARPES	73
2.8 Theoretical DFT	76
<b>Chapter 3: Defect induced Ferromagnetic Ordering and Room Temperature     Negative Magnetoresistance in MoTeP</b>	<b>77-96</b>
3.1 Introduction	79
3.2 Methods	80
3.2.1 Structural Characterization	80
3.2.2 Material Characterization	80
3.2.3 DFT	81
3.3 Results and discussions	81

## Contents

---

3.3.1 Zero field resistivity behaviour	81
3.3.2 Hall effect study	83
3.3.3 Magnetic behaviour	86
3.3.4 Effect of magnetic field on longitudinal resistivity	87
3.3.5 DFT calculation	92
3.3.6 Temperature dependent Raman measurements	95
3.4 Conclusion	95
<b>Chapter 4.A: Experimental and Theoretical Revelation of a Unique Band Topology in <math>\text{Sb}_2\text{Te}_3</math> Topological Insulator by substitution of Cu- A High Pressure Study</b>	<b>97-115</b>
4.A.1 Introduction	99
4.A.2 Methods	101
4.A.2.1 Computational details	101
4.A.3 Results and Discussion	101
4.A.3.1 XRD	101
4.A.3.2 Raman measurements	109
4.A.3.3 Theoretical discussions	112
4.A.4 Conclusions	114
<b>Chapter 4.B: Pressure induced topological and structural transitions in iron and sulphur doped <math>\text{Sb}_2\text{Te}_3</math></b>	<b>117-124</b>
4.B.1 Introduction	119
4.B.2 Results and Discussions	119
4.B.3 Conclusion	124
<b>Chapter 5: Above-Ordering-Temperature Anomalous Hall Effect in A Rare Earth Doped Topological Insulator <math>\text{BiSbTe}_3</math></b>	<b>125-146</b>
5.1 Introduction	127
5.2 Methods	129
5.3 Results and Discussion	129
5.3.1 XRD	130
5.3.2 Resistivity behaviour	130
5.3.3 Field effect on longitudinal resistivity	131
5.3.4 Hall study	132
5.3.5 Magnetic behaviour	137
5.3.6 sdH oscillation	144
5.4 Conclusions	145
<b>Chapter 6.A: Unusual Double Glassy phase and Anomalous Hall effect in S-doped <math>(\text{SbFe})_2\text{Te}_3</math> Topological Insulator</b>	<b>147-166</b>
6.A.1 Introduction	149
6.A.2 Results and Discussions	150
6.A.2.1 XRD	150
6.A.2.2 Resistivity behaviour	151

## Contents

---

6.A.2.3 Magnetic behaviour	153
6.A.2.4 ac susceptibility	157
6.A.2.5 Temperature dependent Raman	163
6.A.2.7 dHvA oscillation	164
6.A.2.7 ARPES	166
<b>Chapter 6.B: Unusual Double Glassy phase and Anomalous Hall effect in S-doped (BiFe)<sub>2</sub>Te<sub>3</sub> Topological Insulator</b>	<b>167-180</b>
6.B.1 Results and Discussions	169
6.B.1.1 XRD	169
6.B.1.2 Resistivity behaviour	169
6.B.1.3 Magnetic behaviour	170
6.B.1.4 ac susceptibility	173
6.B.1.5 Temperature dependent Raman	177
6.B.1.6 ARPES	179
6.B.2 Conclusion	179
<b>Chapter 7.A: Unusual Double Glassy phase and Anomalous Hall effect in S-doped (SbFe)<sub>2</sub>Te<sub>3</sub> Topological Insulator</b>	<b>181-190</b>
7.A.1 Introduction	183
7.A.2 Methods	184
7.A.3 Results and Discussions	184
7.A.4 Conclusion	190
<b>Chapter 7.B: Unusual Double Glassy phase and Anomalous Hall effect in S-doped (BiFe)<sub>2</sub>Te<sub>3</sub> Topological Insulator</b>	<b>191-200</b>
7.B.1 Introduction	191
7.B.2 Methods	194
7.B.3 Results and Discussions	194
7.B.4 Conclusion	200
<b>Chapter 8: Summary and future perspectives</b>	<b>201-208</b>
8.1 Summary	203
8.2 Future perspectives	205
8.3 Applications	206
<b>References</b>	<b>209-238</b>
<b>List of Publications</b>	<b>239</b>
<b>Schools / Meetings / Workshops / Conference Attended</b>	<b>240</b>

## List of Figures

---

**Figure 1.1:** Schematics of electronic bands in various solid-state materials. In semiconductors/insulators, the valence and conduction bands are separated by an energy gap. In metals, the valence and conduction bands overlap each other. In topological insulators, after band inversion, the valence and conduction bands are separated by the band gap, leaving behind conducting topological surface states in the form of linearly crossing Dirac cone. 35

**Figure 1.2:** Semiclassical description of integer quantum Hall state. 37

**Figure 1.3:** Geometrical objects with different topological classes represented by the genus numbers. 38

**Figure 1.4:** The interface between a quantum Hall state and an insulator has chiral edge mode. (a) The skipping cyclotron orbits. (b) The electronic structure of a semi-infinite strip described by the Haldane model. A single edge state connects the valence band to the conduction band. 40

**Figure 1.5** Spatial separation is at the heart of both the quantum Hall (QH) and the quantum spin Hall (QSH) effects. (a) A spinless one-dimensional system has both a forward and a backward mover. Those two basic degrees of freedom are spatially separated in a QH bar, as illustrated by the symbolic equation “ $2 = 1 + 1$ .” The upper edge contains only a forward mover and the lower edge has only a backward mover. The states are robust: They will go around an impurity without scattering. (b) A spinful 1D system has four basic channels, which are spatially separated in a QSH bar: The upper edge contains a forward mover with up spin and a backward mover with down spin, and conversely for the lower edge. That separation is illustrated by the symbolic equation “ $4 = 2 + 2$ .” 41

**Figure 1.6** (Color online) Edge and surface states of topological insulators with Dirac dispersions. (a) Schematic real-space picture of the 1D helical edge state of a 2D TI. (b) Energy dispersion of the spin non-degenerate edge state of a 2D TI forming a 1D Dirac cone. (c) Schematic real-space picture of the 2D helical surface state of a 3D TI. (d) Energy dispersion of the spin non-degenerate surface state of a 3D TI forming a 2D Dirac cone; due to the helical spin polarization, back scattering from  $k$  to  $-k$  is prohibited. 43

**Figure 1.7** Schematic illustration of Dirac node, Weyl node and Nodal line/ ring in momentum space. (a) Schematic of a Dirac semimetal where the bands are linearly dispersed around the Dirac point. The Dirac point is shown by the green dot. (b) Weyl semimetal, in which the Weyl points with opposite chirality are connected by the characteristic Fermi arc. The Weyl points are shown by the green dot and Fermi arc is shown by the black dotted line. (c) Nodal line semimetals where valence and conduction bands cross along special lines in momentum space forming either a ring-shaped line or 1D line, shown by the green circle/line. 45

**Figure 1.8** (a) Dispersions for type-I Weyl fermion near  $E_F$ . The Weyl points (WP) are labelled by yellow and green dots, (b) Type-II Weyl semimetal with electron and hole pockets touching at two different energies, Crystal structures of  $\text{MoTe}_2$  (c) in the  $1T'$  and in (d) $T_d$  phases. 47

## List of Figures

---

**Figure 1.9** (a) 3D bulk BZ and the projected (001) surface BZ of MoTe<sub>2</sub>. Weyl points with positive and negative monopole charges are displayed as green and gray dots. (b) Calculated fine band structure of MoTe<sub>2</sub> along the K-K' direction crossing two types of Weyl points. (c) Calculated spectral intensity maps of MoTe<sub>2</sub> at E<sub>F</sub> +5 meV. (d) Calculated spectral intensity maps of MoTe<sub>2</sub> at E<sub>F</sub> (shifted by -0.02 eV to account for the slight hole doping). The white dashed boxes indicate the regions of interest shown in (c). (e) ARPES intensity maps of MoTe<sub>2</sub> measured at E<sub>F</sub> with a 6.3 eV laser. (f), (g) ARPES intensity plot and the calculated electronic structure of Mo<sub>0.25</sub>W<sub>0.75</sub>Te<sub>2</sub> at k<sub>x</sub> ~ k<sub>w</sub> along the k<sub>y</sub> direction. The red lines indicate the energy positions of the surface band bottom, the W1 point, and the W2 point, respectively. 49

**Figure 1.10:** Five mono atomic planes of a quintuple layer of Bi<sub>2</sub>Te<sub>3</sub>/Sb<sub>2</sub>Te<sub>3</sub>. 55

**Figure 1.11** Schematic crystal structures of Sb<sub>2</sub>Te<sub>3</sub> polymorphs: (a) α-Sb<sub>2</sub>Te<sub>3</sub>; (b) β-Sb<sub>2</sub>Te<sub>3</sub>; (c) γ-Sb<sub>2</sub>Te<sub>3</sub> and (d) δ-Sb<sub>2</sub>Te<sub>3</sub>. 56

**Figure 2.1:** (a) Photograph of cleaved crystal sample, (b) schematic of CVT technique. 60

**Figure 2.2:** (a) Schematic of x-ray diffraction by crystallographic planes (b) Image of Rigaku Mini Flex II DESKTOP lab based XRD set up. 62

**Figure 2.3:** Schematic for (a) longitudinal resistivity measurements using four-probe geometry and (b) Hall resistivity measurements using four-probe geometry. The magnetic field is applied orthogonally to the applied electric current (I). 65

**Figure 2.4:** The Physical property measurement system (PPMS) set up at UGC-DAE, Kalapakkam node. 66

**Figure 2.5:** Van der Pauw contact configuration for measuring the resistivity: **upper panel**-longitudinal resistivity (MR), **lower panel**- transverse resistivity (Hall). 67

**Figure 2.6:** (a) Image of Quantum Design MPMS3 of CIFIC, IIT (BHU), (b) Schematic diagram of SQUID-VSM detection system. 68

**Figure 2.7:** (a) Energy-level diagram presenting the states involved in Raman scattering process, (b) Schematic diagram of Raman active vibrational modes. 70

**Figure 2.8:** Schematic of a diamond-anvil-cell (DAC) used for generating high pressure. 72

**Figure 2.9:** Schematic of ARPES measurements, **(b)** Energy and momentum dependence of the local density of states for (a)Sb<sub>2</sub>Se<sub>3</sub>, Sb<sub>2</sub>Te<sub>3</sub>, Bi<sub>2</sub>Se<sub>3</sub>, and Bi<sub>2</sub>Te<sub>3</sub> on the [111] surface. The red and blue regions indicate bulk energy bands and bulk band gaps, respectively. The red lines, dispersing in the bulk gap around the Γ point, are the surface states. 75

**Figure 3.1:** **(a)** Thermal hysteresis of temperature dependent resistivity of 1T' MoTeP, **inset:** low temperature resistivity data, orange solid line is a fit of electron-electron and electron-phonon scattering terms  $\rho(T) = \rho_0 + aT^2 + bT^5$ , **(b)** temperature evolution of  $\rho_{xx}$  and  $d\rho_{xx}/dT$  at zero magnetic field, **(c)** Field dependence of Hall data  $\rho_{xy}$  at various temperatures, **inset:** measurement geometry, **(d)** low- field low-temperature

## List of Figures

---

conductivity data, solid orange line shows HLN fitting to  $\Delta\sigma(e^2/h)$  at various temperatures. 82

**Figure 3.2:** (a), (b) Field dependence of Hall conductivity  $\sigma_{xy}$  and longitudinal conductivity  $\sigma_{xx}$  at 2,50,100 and 200K, orange solid lines are their respective two-carrier model fit with equations 1 and 3, (c) density of electrons  $n_e$  (black circle) and density of hole  $n_h$  (red circles) as a function of temperature extracted from  $\sigma_{xy}$ , **inset:** ratio of  $n_h$  and  $n_e$  as a function of temperature, (d) electron mobility  $\mu_e$  (black circle) and hole mobility  $\mu_h$  (red circles) and their ratio  $\mu_h/\mu_e$ , **inset:** as a function of temperature. 85

**Figure 3.3:** (a) Magnetic field dependent MR% at various temperatures ranging from 2K-300K, inset shows 2K MR% with a power law fit (orange solid line), (b) clear pictorial view of positive MR at low field and negative MR at high field for 300K data, **inset:** measurement geometry, (c) Kohler's scaling of MR% as a function of  $B/\rho_0$  up to 300K, **inset:** Kohler plot on logarithmic scale up to 200K, (d) M-B magnetic hysteresis curve taken at 5K and 300K. 88

**Figure 3.4:** (a) Bulk band structure of  $T_d$ -MoTeP with inclusion of SOC, (b) Spin-resolved Total DOS for defect induced MoTeP. 92

**Figure 3.5:** (a) Mo-d band contribution in bandstructure. 93

**Figure 3.6:** (a)-(c) Te-p band contribution in bandstructure, (d)-(f) P-p band contribution in bandstructure. 94

**Figure 3.7:** Temperature dependent Raman spectra during (a) cooling and (b) heating cycle. The newly obtained mode is noted by arrow at  $117.63 \text{ cm}^{-1}$  indicating the presence of  $T_d$  phase. 94

**Figure 3.8** (a) Magnetic moment as a function of temperature in ZFC and FC cycle; (b) MFM image taken at room temperature with scan areas  $5 \times 5 \text{ }\mu\text{m}^2$ . 95

**Figure 4.A.1:** (a) ADXRD patterns collected at various pressures for  $\text{Sb}_{1.9}\text{Cu}_{0.1}\text{Te}_3$ . The new peaks are marked with arrows, for phases II (C2/m), III(C2/c), and IV(Im-3m), respectively, Rietveld full-profile refinements of the diffraction patterns collected on compression at (b) 0.26 GPa (Rhombohedral R-3m phase), Le-Bail refinements of the diffraction patterns (c) 9.8 GPa (Monoclinic C2/m phase) and (d) 16.77 GPa (Monoclinic C2/c phase) and (e) 31.48 GPa (disordered cubic Im-3m phase) the difference plot is given below. The difference plot is shown in blue. Background is shown as green and the vertical marks give the individual phases of sample, Cu and W. 102

**Figure 4.A.2:** (a)  $c/a$  ratio as a function of pressure for ambient rhombohedral (R-3m) phase, 3 different colors indicate slope changes at those regions, (b) The volume as a function of pressure for initial rhombohedral phase with error bars. The dashed lines are the fitting results according to the third-order Birch-Murnaghan (red) and Murnaghan (blue) EoS, (c) Pressure dependence of the volume per atom ( $V/\text{atom}$ ) for all the four phases. 103

## List of Figures

---

**Figure 4.A.3:** Fit of compressibility with universal equation of state; blue solid line is (a) fit with Vinet EOS, (b) fit with Holzapfel EOS. 106

**Figure 4.A.4:** (a) Bond length of Te2-Sb, Te1-Sb and Te2-Te2 as a function of pressure, (b) angle of succession Te1-Sb-Te2 vs pressure, (c) vertical distance between intra-layer and interlayer. 107

**Figure 4.A.5:** (a) Schematic of  $\text{Sb}_{1.9}\text{Cu}_{0.1}\text{Te}_3$  at various phases I(R-3m), II(C2/m), III(C2/c), IV(Im-3m) with pressure. 108

**Figure 4.A.6:** Experimental Raman spectra of  $\text{Sb}_{1.9}\text{Cu}_{0.1}\text{Te}_3$  at pressures (a) 0.1 MPa - 10 GPa, (b) 11.3 - 30 GPa, (c) Pressure dependence of the Raman frequencies, the vertical dashed lines are an estimation of the pressure at which the electronic and structural phase transitions occur, blue hollow square and green crossed circles are for one run, red solid squares and magenta solid circles are for another run of Raman measurements. 110

**Figure 4.A.7:** (a) Bulk bandstructure of  $\text{Sb}_{1.9}\text{Cu}_{0.1}\text{Te}_3$  at 0 GPa, (b) 0.26 GPa; inset: magnifying view at  $\Gamma$ -point shown, (c) 2.87 GPa. The Fermi level is set to zero. 112

**Figure 4.A.8:** Projected DOS and inset: Total DOS at (a) 0 GPa, (b) 0.26 GPa and (c) 2.87 GPa. The Fermi level is set to zero. 114

**Figure 4.B.1:** Schematics of  $\text{Sb}_{1.9}\text{Fe}_{0.1}\text{S}_{0.15}\text{Te}_{2.85}$  structures at different pressures: (a) ambient R-3m, C2/m above 8.9 GPa, C2/c above 14.1 GPa, and  $\text{Im}\bar{3}m$  above 15.1 GPa, (b) Single crystal XRD of  $\text{Sb}_{1.9}\text{Fe}_{0.1}\text{S}_{0.15}\text{Te}_{2.85}$ . 120

**Figure 4.B.2:** (a) ADXRD of  $\text{Sb}_{1.9}\text{Fe}_{0.1}\text{S}_{0.15}\text{Te}_{2.85}$  up to 32 GPa, (b) c/a anomaly with pressure: solid red circles show c/a anomaly with pressure, hollow circles show comparison with pure  $\text{Sb}_2\text{Te}_3$ . 121

**Figure 4.B.3:** (a) Volume as a function of pressure for all 4 phases, (b) Universal equation of state  $\ln H$  as a function of  $1-X$ , (c) Fitting of 3<sup>rd</sup> order Birch-Murnaghan EOS on rhombohedral phase. 122

**Figure 5.1:** (a) Single crystal XRD and inset: powder XRD with Le-Bail refinement of  $(\text{BiSbDy})_2\text{Te}_3$ , (b) Fitting of electron-electron interaction term  $A+BT^n$  on the low temperature part of the resistivity data  $\rho_{xx}$ . 130

**Figure 5.2:** (a) Resistivity evolution with temperature in the range 2-300K (pink), the derivative of  $\rho_{xx}$  data exhibits a jump at 44.2K (green), (b) Hall data as a function of field at various temperatures ranging from 2-100K, (c) the extracted carrier density ( $n_e$ ) and mobility ( $\mu_e$ ) as a function of temperature, (d) The anomalous Hall part after extracting the linear part from the total Hall data. 132

**Figure 5.3:** (a) MR% data with field at various temperatures 2K, 5K, 10K, 25K, 50K, 100K, (b) The fitting of MR% data with the Kohler's scaling  $B/\rho_{xx}(0)$  scaling, (c) The variation of magnetization with field at various temperatures

## List of Figures

2K,10K,50K,100K,150K, **(d)** The magnetization evolution with temperatures in ZFC and FC cycle. 134

**Figure 5.4 (a)** The schematic of the different skew scattering mechanism in a clean FM, spin glass and cluster glass systems, **(b)** The anomalous Hall conductivity as a function of longitudinal conductivity,  $\sigma_{xy} \propto \sigma_{xx}$  scaling showing skew scattering behaviour, **(c)** the anomalous Hall angle as a function of temperature. 138

**Figure 5.5: (a)** The AC susceptibility **(a)** real part and **(b)** imaginary part as a function of temperature at different frequencies, **(c)** The anomalous and Hall conductivity as a function of temperature, **(c)** frequency vs  $T_f$  plot, the best fit shows Dynamic fitting, **(d)** frequency vs  $T_f$  plot, the red line shows VF fitting. 140

**Figure 5.6: (a)**The frequency dependence of freezing temperature plotted as a  $\ln(\tau)$  vs  $\ln(t)$ , where reduced temperature  $t = (T_f - T_{SG})/T_{SG}$ , the red line represents the linear fit to extract  $z\nu$  and  $\tau$ , **(b)**  $\ln(\nu)$  vs  $1/T_f$ , the red line denotes the Arrhenius fitting to extract the thermal activation energy  $E_A$  and characteristic attempt frequency  $f_0$ , **(c)**  $T_f$  vs  $100/\ln(f_0/f)$ , the solid line represents the linear fit to evaluate  $E_A$  and intercluster interaction strength  $T_0$ , **(d)**  $\ln(\nu)$  vs  $1/(T_f - T_0)$ , the red line denotes the linear fit to extract the thermal activation energy  $E_A$  and  $\tau_0$ . 143

**Figure 5.7 (a)** Contour plot of  $\sigma_{xy}$  in the B–T space with the magnetic phase diagram consisting of the antiferromagnetic (AFM) and paramagnetic (PM) phases, **(b)** the bandstructure of Dy doped BiSbTe<sub>3</sub> system. 144

**Figure 5.8:(a)** FFT of the original resistivity  $\rho_{xx}$  vs  $1/B$  data to extract the particular frequency of the oscillation, this particular frequency(50T) is proportional to the area of the Fermi, and **(b)** inverse FFT to obtain 50T frequency signal in time scale, red solid line shows Landau Fan diagram to extract the phase and frequency of the signal. 145

**Figure 6.A.1: (a)** Single crystal XRD pattern of Sb<sub>1.9</sub>Fe<sub>0.1</sub>So<sub>0.15</sub>Te<sub>2.85</sub>, **(b)**resistivity evolution with temperature at zero magnetic field, **(c)**MR% at 2K for B||I and B⊥I configuration, **(d)** Hall resistivity at 2K, 10K, 25K, 50K and 100K, **(e)** AHE effect at 2K, 10K, 25K, 50K and 100K, **(f)** density and mobility evolution with temperature. 151

**Figure 6.A.2: (a)** dc magnetization vs temperature for Sb<sub>1.9</sub>Fe<sub>0.1</sub>So<sub>0.15</sub>Te<sub>2.85</sub> measured between 2 and 350 K at 100 Oe, 0.1T, and 0.4T, **(b)** ZFC and FC curves for 100 Oe, **(c)** dM/dT for 100 Oe ZFC curve to obtain the transition temperatures from inflection points, **(d)** Field dependence of magnetization measured at different temperatures, Temperature dependence of the **(e)** real ( $\chi'$ ) and **(f)** imaginary ( $\chi''$ ) components of the ac susceptibility measured at frequencies varying from 5 to 500 Hz. 153

**Figure 6.A.3: (a)** The ZFC and FC susceptibilities vs T measured at H = 0.1 T, **(b)** the log-log plot of the M(T) curve along with the linear fits at low temperature, **inset:** evolution of magnetization as a function of field at 2K for Sb<sub>1.9</sub>Fe<sub>0.1</sub>Te<sub>3</sub>. 154

**Figure 6.A.4:** Temperature dependent **(a)** Raman spectra, **(b)** 3D plot to see the clear variation between different modes, **(c)**Temperature evolution of the Raman shift of the E<sub>g</sub> mode, and **(d)** M1 mode of Sb<sub>1.9</sub>Fe<sub>0.1</sub>So<sub>0.15</sub>Te<sub>2.85</sub>. 157

## List of Figures

**Figure 6.A.5:** Dynamic scaling (a), (b) and Vogel-Fulcher (c), (d) fits of the “ $T_f$  vs  $f$ ” curve respectively for  $T_{f1}$  and  $T_{f2}$  for  $Sb_{1.9}Fe_{0.1}S_{0.15}Te_{2.85}$ . 159

**Figure 6.A.6:** (a) Time dependence of thermoremanent magnetization at 25 K for 0.1T cooling field and wait time of 100s. The solid line is the best fit for KWW function to the data, (b) powder XRD pattern and its Rietveld refinement for the sample  $Sb_{1.9}Fe_{0.1}S_{0.15}Te_{2.85}$ . 161

**Figure 6.A.7:** (a) dHvA oscillation in the M-H data at low temperature and high magnetic field, (b) FFT amplitude data on frequency scale at 2K & 5K, 5 frequencies  $F_\alpha \sim 40T$ ,  $F_\gamma \sim 60T$ , 2  $F_\alpha \sim 80$ , 2  $F_\beta \sim 100T$ , 3  $F_\beta \sim 150T$  indicating Fermi surfaces of the sample, inverse-FFT with the (c) 60T and (d)  $\sim 150T$  data by using band- pass filter, Landau Fan diagram to obtain the frequency and phase. 165

**Figure 6.A.8:** Temperature dependent angle resolved photoemission spectra taken at (a) 20K, (b) 150K, and (c) 260K with Synchrotron source of 95eV. 166

**Figure 6.B.1:** (a) Single crystal XRD pattern, (b) resistivity evolution with temperature at zero magnetic field, (c) MR% at 2K, 5K, 10K, 25K, 50K, 100K, 200K for B $\perp$ I configuration, (d) Hall resistivity at 2K, 10K, 25K, 50K, 100K and 200K, (e) AHE effect at 2K, 10K, 25K, 50K, 100K and 200K, (f) density and mobility evolution with temperature for  $Bi_{1.9}Fe_{0.1}S_{0.15}Te_{2.85}$ . 169

**Figure 6.B.2:** (a) Temperature dependent dc magnetization  $M(T)$  measured at different applied fields (100 Oe and 0.1T) for ZFC and FC protocols, (b)  $dM/dT$  as a function of temperature, (c) Magnetization as a function of external magnetic field at  $T=5$  K, 100K and 300K (d) real ( $\chi'$ ) and (e) imaginary ( $\chi''$ ) components of the ac susceptibility measured at frequencies varying from 100 to 700 Hz, (f) time dependence of thermoremanent magnetization at 25 K for 0.1T cooling field. The solid line is the best fit for KWW function to the data for  $Bi_{1.9}Fe_{0.1}S_{0.15}Te_{2.85}$ . 171

**Figure 6.B.3:** (a) DC Magnetization measured in ZFC and FC protocol taken at 100 Oe. Inset:  $M(H)$  at 2K and 300K (b) The log-log plot of the  $\chi_{dc}^{-1}$  vs temperature at 100Oe, Inset shows the suppression of GP at higher field (1000 Oe) for  $Bi_{1.9}Fe_{0.1}Te_3$ . 172

**Figure 6.B.4:** Dynamic scaling (a), (b) and Vogel-Fulcher (c), (d) fits of the “ $T_f$  vs  $f$ ” curve respectively for  $T_{f1}$  and  $T_{f2}$  of  $Bi_{1.9}Fe_{0.1}S_{0.15}Te_{2.85}$ . 175

**Figure 6.B.5:** (a) Powder XRD pattern of  $Bi_{1.9}Fe_{0.1}S_{0.15}Te_{2.85}$ , (b) single crystal XRD and (c) powder XRD pattern of  $Bi_{1.9}Fe_{0.1}Te_{2.85}$ . 176

**Figure 6.B.6:** Temperature dependent angle resolved photoemission spectra taken at (a) 20K, (b) 150K, and (c) 260K with Synchrotron source of 95eV. 179

**Figure 7.A.1:** (a) Theoretical band structure of MoTeSe and (b) WTeSe with SOC at ambient conditions. 185

**Figure 7.A.2:** (a) Partial density of states (PDOS) of MoTeSe and (b) WTeSe at ambient pressure; inset: Total density of states (TDOS). 186

## List of Figures

---

- Figure 7.A.3:** (a) PDOS and total DOS (inset) of MoTeSe at 3 GPa and (b) 10 GPa; (c) PDOS and total DOS (inset) of WTeSe at 3 GPa and (d) 10 GPa. 187
- Figure 7.A.4** (a) Theoretically obtained band structure of MoTeSe at 3 GPa and (c) 10 GPa; (b) WTeSe at 3 GPa and (d) 10 GPa. 188
- Figure 7.A.5:** (a) Evolution of lattice parameters a, b and c with pressure for MoTeSe and (c) WTeSe; (b) Volume as a function of pressure and the fitting of P-V data with 3<sup>rd</sup> order Birch-Murnaghan and Murnaghan equation of state for MoTeSe and (d) WTeSe. 189
- Figure 7.B.1:** Crystal structure of Sb<sub>2</sub>Te<sub>3</sub>. 195
- Figure 7.B.2:** Bandstructure of Sb<sub>2</sub>Te<sub>3</sub> taking LDA approximation (a) without SOC; (b) with SOC. 197
- Figure 7.B.3:** Bandstructure of Sb<sub>2</sub>Te<sub>3</sub> taking GGA approximation (a) at ambient pressure; (b) at 2GPa; (c) Partial and total DOS of Sb<sub>2</sub>Te<sub>3</sub> at ambient pressure; (d) at 2 GPa. 198
- Figure 7.B.4:** Bandstructure of Sb<sub>2</sub>Te<sub>3</sub> taking GGA approximation (a) at 7GPa pressure; (b) Comparison of lattice parameters with pressure. 199
- Figure 7.B.5:** (a) Volume as a function of pressure and the fitting of P-V data with 3<sup>rd</sup> order Birch-Murnaghan and Murnaghan equation of state for Sb<sub>2</sub>Te<sub>3</sub>; (b) c/a ratio as a function of pressure. 199
- Figure 7.B.6:** Electronic structure of the surface of Sb<sub>2</sub>Te<sub>3</sub> along its (111) surface at (a) 0 pressure and (b) 7 GPa. The electronic states forming the Dirac cone have been marked with blue circle. 200

## List of Tables

---

<b>Table-3.1:</b> The values of $\alpha$ extracted from HLN fitting.	91
<b>Table 4.A.1:</b> Comparison of experimental ETT and structural transitions (GPa) observed in various TIs.	104
<b>Table 4.A.2:</b> Lattice parameters and bulk modulus (obtained from BM EOS) for our experimental results of $\alpha$ -phase are compared with earlier published results.	105
<b>Table 4.B.1:</b> The lattice parameters and angles for different phases. Bulk modulus and its derivative are also depicted for initial phase.	123
<b>Table 6.A.1:</b> Parameters obtained from the ac susceptibility analysis for $T_{f1}$ and $T_{f2}$ .	160
<b>Table 6.A.2:</b> Parameters obtained from the ac susceptibility analysis for $T_{f1}$ and $T_{f2}$ .	160
<b>Table 6.B.1:</b> Parameters obtained from the Dynamic fitting analysis for $T_{G2}$ .	175
<b>Table 6.B.2:</b> Parameters obtained from the V-F fitting analysis for $T_{G2}$ .	175
<b>Table 7.A.1:</b> a comparative study of electronic and structural transition in $MX_2$ class of materials are given.	186
<b>Table 7.B.1:</b> Comparisons of ETT pressure in different TI materials.	198



## Preface

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In this thesis, we have investigated the topological nature, Fermi surface properties, magnetic behaviour, electronic transitions, structural transitions, and electronic transport properties of several doped Topological compounds like Cu doped  $\text{Sb}_2\text{Te}_3$ , Fe and S co-doped  $\text{Bi}_2\text{Te}_3$ , Fe and S co-doped  $\text{Sb}_2\text{Te}_3$ , Dy doped  $\text{BiSbTe}_3$  and P doped  $\text{MoTe}_2$  under different conditions. These materials provide an ideal playground to tune the lattice dynamics, Fermiology, spin dynamics and create exceptional quantum phenomena due to the effect of dopant and its interaction with the host element. Each of these systems we studied, represent some exotic and new features with rich physics, thus make them extraordinary from the parent compound. The precise choice of dopant allows us to nurture the physics behind, and fundamentally interesting from Physics and Material science point of view. The motivation behind each work has been elaborated in the respective chapters.

In **Chapter 1**, we have revisited the theoretical and experimental discoveries that led to our current understanding of topological band theory. These breakthroughs spanned decades, and each of them proved to be a significant step in quantum condensed matter physics. We begin with the concept of quantum Hall state which is the onset of the historical developments of Topological Insulators (TIs). The integer quantum Hall effect (IQHE) is then observed, followed by the establishment of Quantum spin Hall insulator (QSHI) and topological order in real systems. The physics of TIs and Topological semimetals (TSMs), specifically Weyl Semimetals (WSMs) have been articulated in detail. Following that, in chronological sequence, we presented the fascinating properties of TIs and the effect of magnetism, pressure and temperature on the Topological property. The basics of various important quantum features that we observed in studying the materials are also explained to understand the physics behind them. This comprises the effect of magnetism- anomalous Hall effect, the intrinsic and extrinsic mechanism behind AHE, spin chirality induced skew scattering beyond the usual scattering effect, magnetic frustration including spin glass or

## Preface

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cluster glass and also the effect of high pressure like electronic topological transition (ETT), metal-semiconductor transition, structural transitions when we put different dopants into the TI or TSMs system. This chapter also deals with other issues like the concept of Berry phase, Shubnikov-de Haas (SdH), de Haas-van Alphen (dHvA) oscillation, weak antilocalization (WAL)-weak localization (WL) effect, the protection of Topological surface state etc. Finally, we highlighted the important findings of this thesis and emphasised how these works prompted us to investigate such unique quantum phases of matter.

In **Chapter 2** we discuss the synthesis and characterization techniques that are used throughout this thesis. This includes how the single crystal Topological insulators and Weyl semimetals are grown using advanced technology. Some specific choices that made in order to play with the electronic structures of those materials are also mentioned. The characterization specifications for operation are also discussed. The structural analysis was performed with single crystal and powder XRD ( $\text{CuK}\alpha$   $\lambda \sim 1.54 \text{ \AA}$ ), the structural transition or changes in electronic topology of the Fermi surface was captured with synchrotron angle dispersive X-Ray diffraction ADXRD ( $\lambda \sim 0.7842 \text{ \AA}$ ), pressure dependent Raman (Diode pumped solid state laser  $\sim 532 \text{ nm}$ ), temperature dependent Raman (He-Ne laser  $\sim 633 \text{ nm}$ ). The electronic behaviour was analysed by transport studies including transverse and longitudinal resistivities and performed with the help of physical property measurement system (PPMS). To shed light on some particular phenomena, magnetic behaviour measured with magnetic properties measurement system (MPMS). To delve into the materials' complex band topology and relate that with Fermi surface, dHvA, SdH and angle resolved photo emission spectroscopy (ARPES) are executed carefully.

In **Chapter 3** the electronic properties of a near-perfect compensated semimetal  $\text{MoTeP}$  were investigated using longitudinal and transverse resistivity (Hall) measurements. A

## Preface

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structural transition along with an electronic transition was confirmed with temperature dependent resistivity and Raman measurements. The crossover from low-field positive magnetoresistance (MR) to high field negative MR at room temperature is attributed to suppression of spin scattering effect. This spin scattering suppression is led by defect induced ferromagnetism as confirmed from the magnetic M-T, M-H data. This is further verified by the spin polarized density of states calculation by adding some defects into the crystal structure.

In **Chapter 4** we unfold a unique semiconductor to metal transition, an electronic topological transition (ETT) and 3 structural transitions (Rhombohedral→monoclinic C2/m→ another monoclinic C2/c → disordered cubic Im-3m phase) in Cu doped Sb<sub>2</sub>Te<sub>3</sub> while high pressure measurements. The structural phases are analyzed by Reitveld/Le-Bail refinement at various pressure. Importantly the semiconductor to metal transition occurred at a pressure below 1 GPa which is lowest amongst the TI family of compounds (Bi<sub>2</sub>Te<sub>3</sub>, Sb<sub>2</sub>Te<sub>3</sub>, Bi<sub>2</sub>Se<sub>3</sub>). The unusual softening of two newly Raman modes combined with sudden collapse in bond length, angle of succession, intralayer distance and the direct observation of band gap closure from density function theory (DFT) validates this metallic transition. The ETT is found at a lower pressure compared to the parent one and confirmed by *c/a* minimum.

Additionally, we also reveal the high-pressure studies of Fe and S co-doped Sb<sub>2</sub>Te<sub>3</sub> system that emerge one ETT and 3 structural transitions with increasing pressure. Our studies unravel how suitable choice of dopant can lower the ETT pressure. Importantly, the initial rhombohedral phase is not retrieved with removal of pressure, rather transformed into an alloy. These studies indicate that appropriate doping can indeed help us to trap unique states at ambient pressure and can thus help in synthesizing new materials.

## Preface

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**In Chapter 5** we deal with the characterization of the Dy doped  $\text{BiSbTe}_3$  topological insulator. The resistivity measurements demonstrate nonlinearity in the Hall behaviour. Due to the widespread applicability in magnetic sensors, random access memory, and spin logic devices, AHE is gaining tremendous research interest in condensed matter physics. Our findings shed light on the TI  $\text{Bi}_{0.95}\text{Sb}_{0.95}\text{Dy}_{0.1}\text{Te}_3$  with AHE at temperatures much above antiferromagnetic ordering (Neel temperature  $T_N \sim 44\text{K}$ ). Up to magnetic transition temperature it is the concomitant effect of magnetism and the frustrated lattice that realizes this extraordinary effect. The AHE above  $T_N$  is attributed to thermal average of the spin chirality in the system. The present observation exhibits short range spin correlation and noncoplanar spin textures thus possess a large Hall angle compared to the usual limit of scattering. The nontriviality of the material was envisaged by the SdH oscillation study. From the magnetic AC susceptibility study, we aim to confirm the glassy nature at low temperature. Our studies demonstrates that Dy-doped BST is not only a topologically nontrivial material, but exhibit a frustrated cluster spin glass nature at low temperature.

**In Chapter 6** we confirm Topological magnetic structure in Fe and S co-doped Topological insulator  $\text{Sb}_2\text{Te}_3$  and  $\text{Bi}_2\text{Te}_3$ . The systems are characterized with magneto-transport, magnetic AC susceptibility at different frequency, M-T, M-H, dHvA, SdH, temperature dependent Raman and ARPES techniques. A unique combination of disordered glassy phase, competitive FM-AFM interactions and nontrivial topology make the system distinct from other TIs. Topological frustrated magnets, which can host both magnetic frustrations and Dirac quasiparticles, are highly sought after class of compounds. Furthermore, as seen by the quantum oscillation study, the Fermiology changes with doping and produces multiple Fermi pockets, revealing a rich complexity in the underlying electronic structure. We have discussed the impact of those complicated magnetic phases upon the observed

## Preface

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AHE in  $\text{Sb}_{1.9}\text{Fe}_{0.1}\text{Te}_{2.85}\text{S}_{0.15}$  and  $\text{Bi}_{1.9}\text{Fe}_{0.1}\text{Te}_{2.85}\text{S}_{0.15}$  with magnetotransport studies. The in depth dHvA and SdH oscillation complements the ARPES study.

**In Chapter 7** we executed density functional theory (DFT) to address the electronic properties of various compounds under pressure. The idea is to tune electronic properties under extreme conditions and create rich physics and hold them as candidates for optoelectronics, spintronics and nanoelectronics. The electronic character of the band structure and density of states (DOS) exhibit a metallic transition near 3 GPa for both MoTeSe and WTeSe whereas they showed a semimetallic behaviour at ambient condition. The present work depicts a pressure studies up to 10 GPa to explore the lattice parameters, volume changes and c/a anomaly. Out of the two, WTeSe shows a Dirac like dispersion without any band crossings along Z-U symmetry path.

The density functional theory (DFT) calculation shows electronic topological transition (ETT) under the application of pressure in  $\text{Sb}_2\text{Te}_3$  Topological insulator. When pressure is applied conduction band and valence shifts significantly which is indicated as electronic transition of the Fermi surfaces. The band gap between conduction band and valence band reduced at Z-high symmetry point whereas it is observed to enhance at  $\Gamma$ -point with increase in pressure indicating the presence of ETT. Interestingly, we found semiconductor to metal transition near 2 GPa with LDA approximation. The overall change in the Fermi surfaces is found to follow other topological insulators like  $\text{Bi}_2\text{Te}_3$  and  $\text{Bi}_2\text{Se}_3$ . The topologically non-trivial surface state remains unchanged under pressure; however, the bulk band gap reduces.

**In Chapter 8** we briefly discuss the applications of these extraordinary class of materials in the field of optoelectronic devices, p-n junction, superconducting materials, field effect transistor, memory device and spintronics, ultrafast photodetection and quantum

## Preface

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computations. We have also presented the summary of the present thesis with a brief future scope of work.